

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
150V	3.3mΩ@10V	260A



合肥矽普半导体

Siliup Semiconductor Technology Co., Ltd

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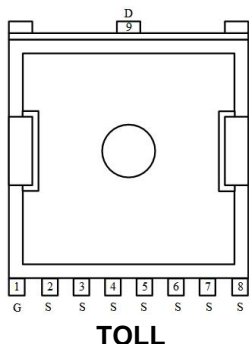
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test
- **AEC-Q101** quality

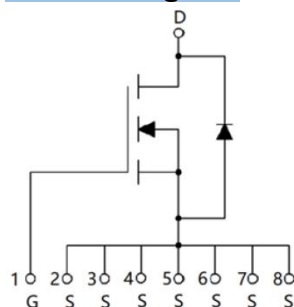
Applications

- PWM Application
- Hard switched and high frequency circuits
- Power Management

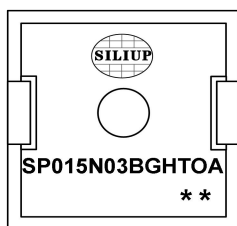
Package



Circuit diagram



Marking



SP015N03BGHTOA : Product code
** : Week code

Order Information

Device	Package	Unit/Tape
SP015N03BGHTOA	TOLL	2000

Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Tc=25°C)	I_D	260	A
Continuous Drain Current (Tc=100°C)	I_D	173	A
Pulsed Drain Current	I_{DM}	1040	A
Single Pulse Avalanche Energy ¹	E_{AS}	1681	mJ
Power Dissipation (Tc=25°C)	P_D	525	W
Power Dissipation (Tc=100°C)	P_D	262.5	W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	0.28	°C/W
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	42	°C/W
Storage Temperature Range	T_{STG}	-55 to 175	°C
Operating Junction Temperature Range	T_J	-55 to 175	°C

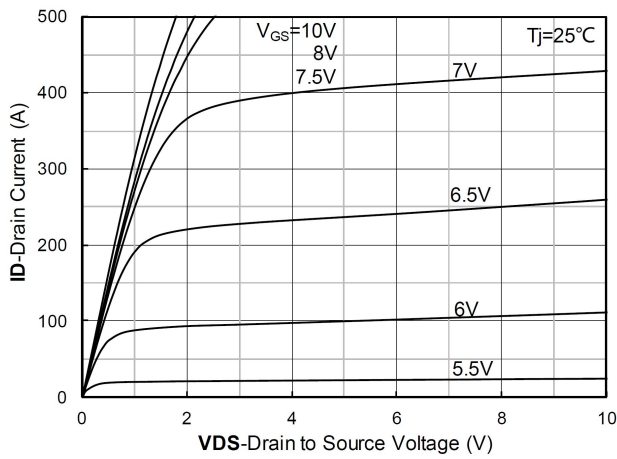
Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	ID=250μA , VGS=0V	150	170	-	V
Drain-Source Leakage Current	Idss	VDS=150V , VGS=0V	-	-	1	uA
Gate-Source Leakage Current	IGSS	VGS=±20V , VDS=0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	VDS=VGS , ID=250μA	2.6	3.0	3.4	V
Static Drain-Source On-Resistance	RDS(ON)	VGS=10V , ID=20A	-	3.3	3.8	mΩ
Gate Resistance	RG	VDS=75V , VGS=0V , f=1MHz	-	1.2	-	Ω
Dynamic characteristics						
Input Capacitance	Ciss	VDS=75V , VGS=0V , f=1MHz	-	10402	-	pF
Output Capacitance	Coss		-	635	-	
Reverse Transfer Capacitance	Crss		-	24	-	
Total Gate Charge	Qg	VDS=75V , VGS=10V , ID=20A	-	148	-	nC
Gate-Source Charge	Qgs		-	58	-	
Gate-Drain Charge	Qgd		-	40	-	
Gate Plateau Voltage	Vplateau		-	5.1	-	V
Switching Characteristics						
Turn-On Delay Time	Td(on)	VDD=75V , VGS=10V , RG=3.0Ω , ID=20A	-	40	-	nS
Rise Time	Tr		-	72	-	
Turn-Off Delay Time	Td(off)		-	108	-	
Fall Time	Tf		-	58	-	
Diode Characteristics						
Diode Forward Voltage	VSD	VGS=0V , IS=1A , TJ=25℃	-	-	1.2	V
Maximum Body-Diode Continuous Current	IS		-	-	260	A
Reverse Recovery Time	Trr	IS=15A , di/dt=100A/us , TJ=25℃	-	112	-	nS
Reverse Recovery Charge	Qrr		-	426	-	nC

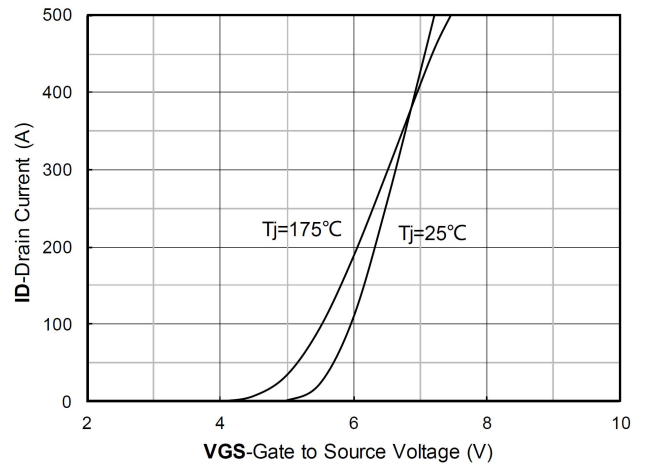
Note :

1. The test condition is $V_{DD}=50V$, $V_{GS}=10V$, $L=0.5mH$, $R_G=25\Omega$

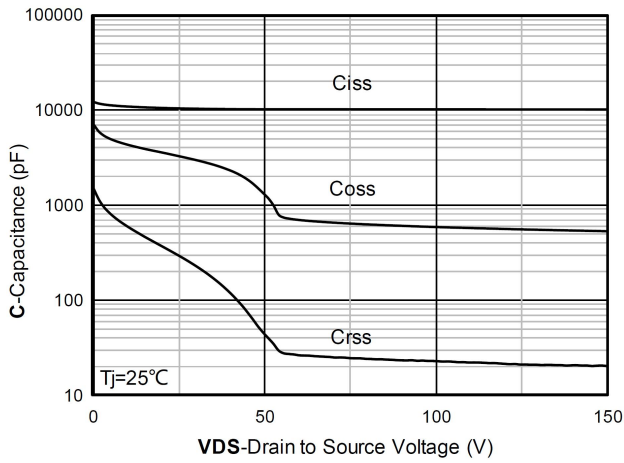
Typical Characteristics



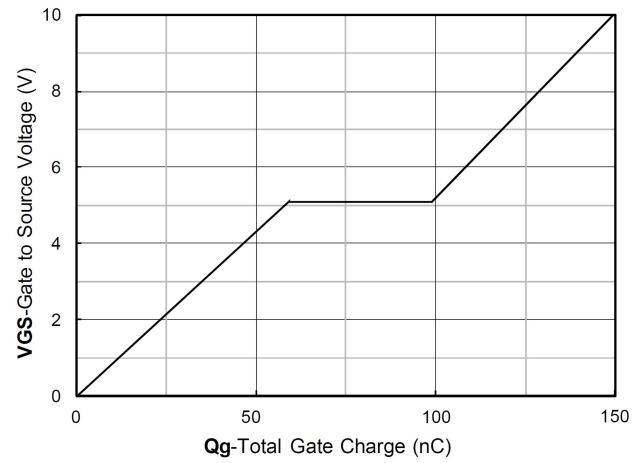
Output Characteristics



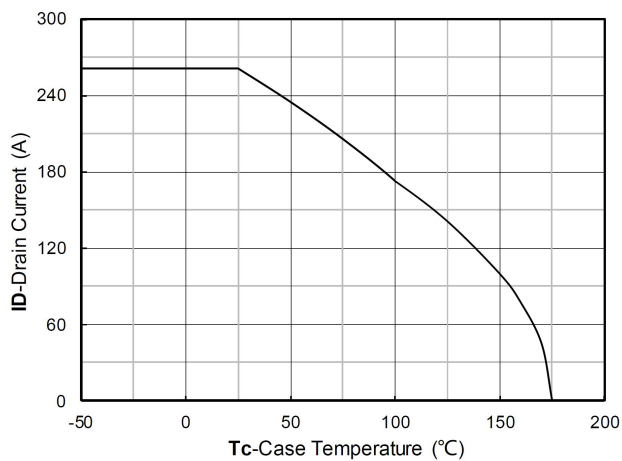
Transfer Characteristics



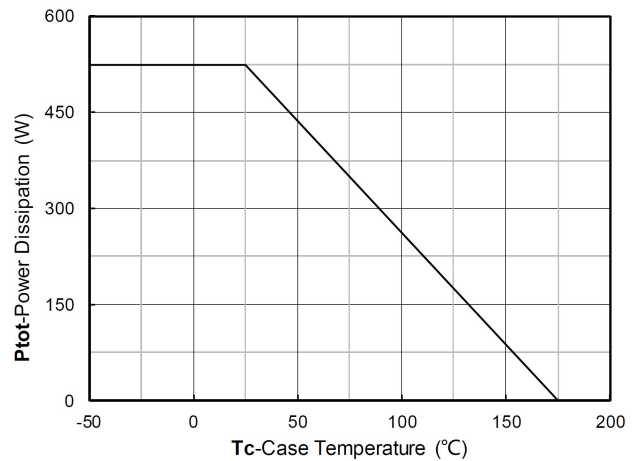
Capacitance Characteristics



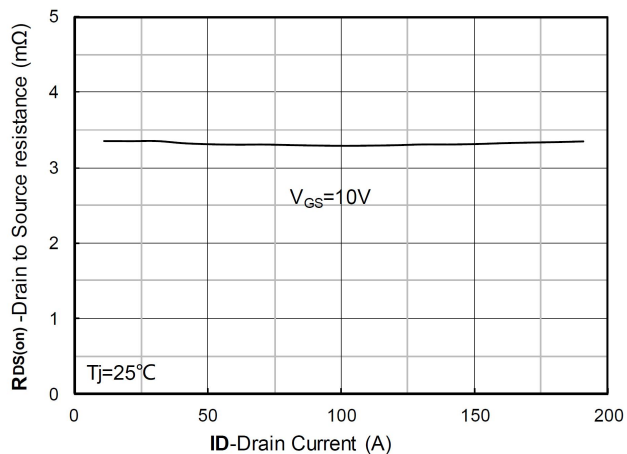
Gate Charge



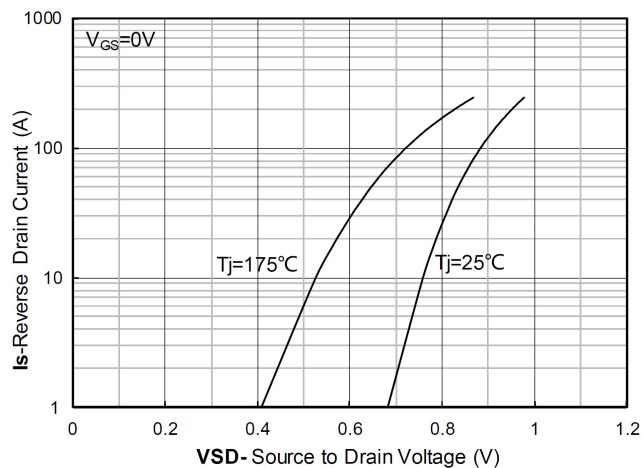
Current dissipation



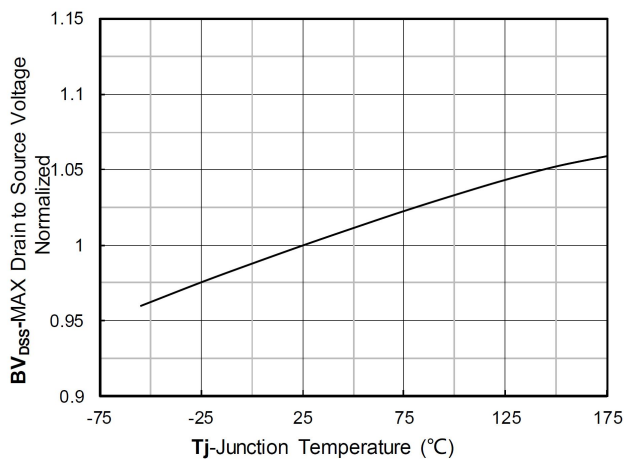
Power dissipation



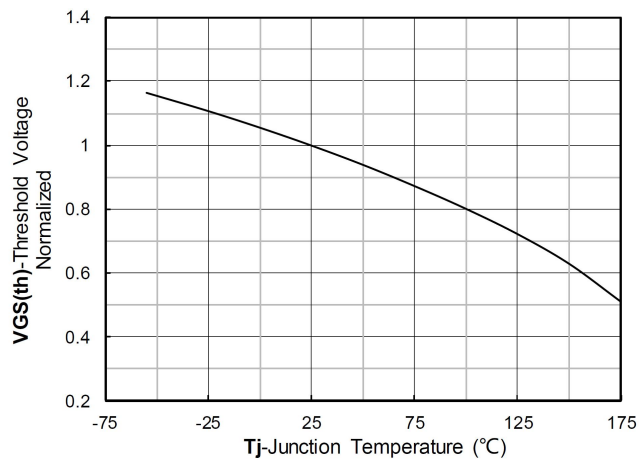
RDS(on) vs. Drain Current



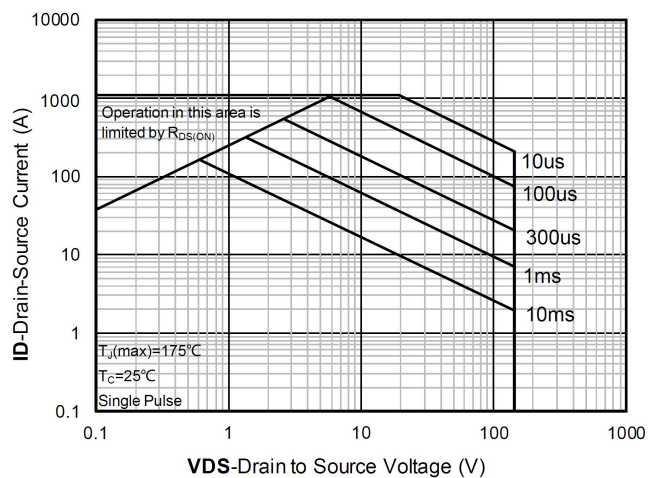
Forward characteristics of reverse diode



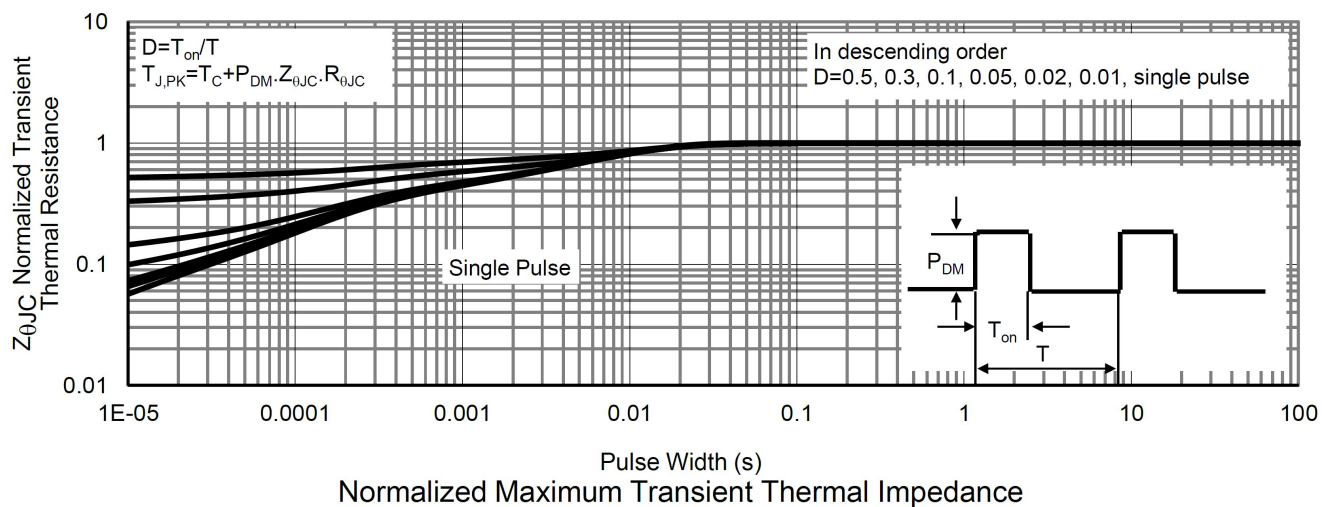
Normalized breakdown voltage

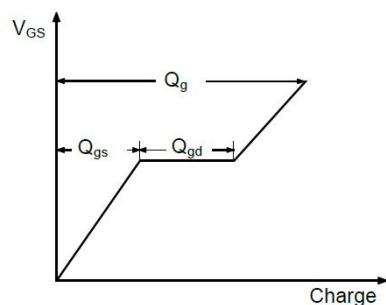
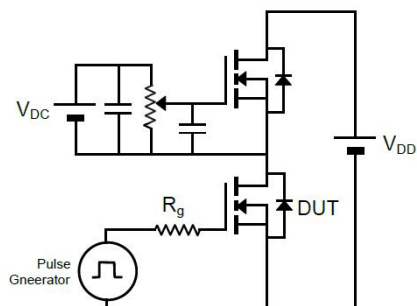
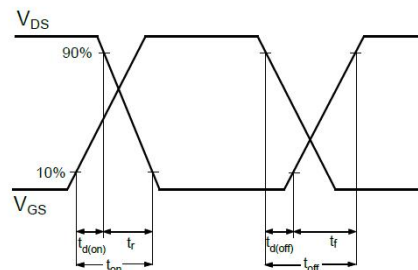
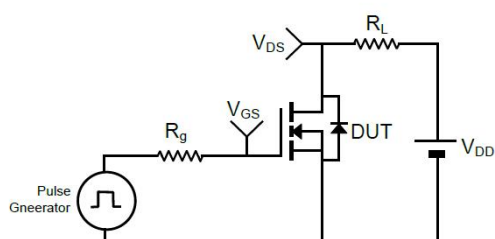
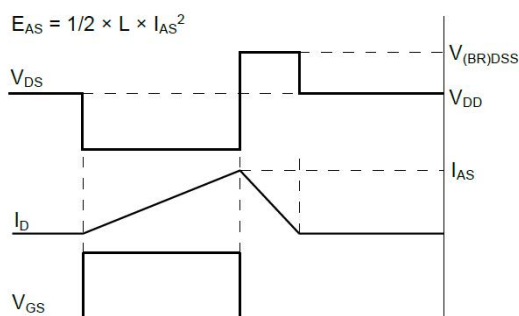
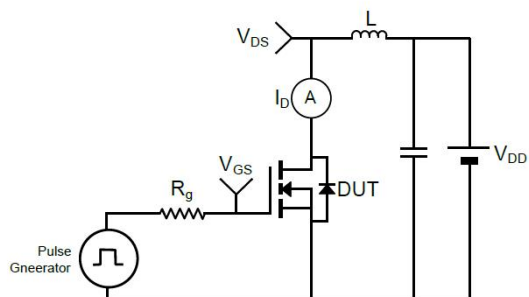
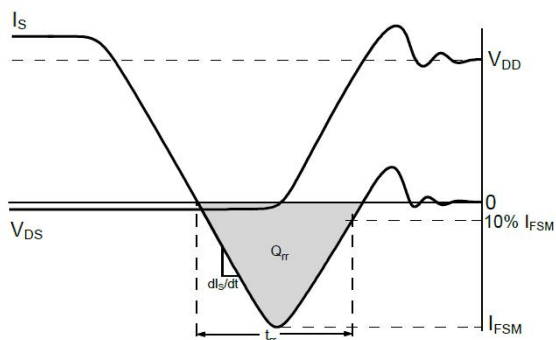
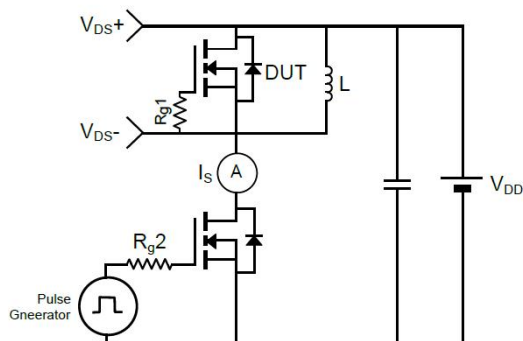


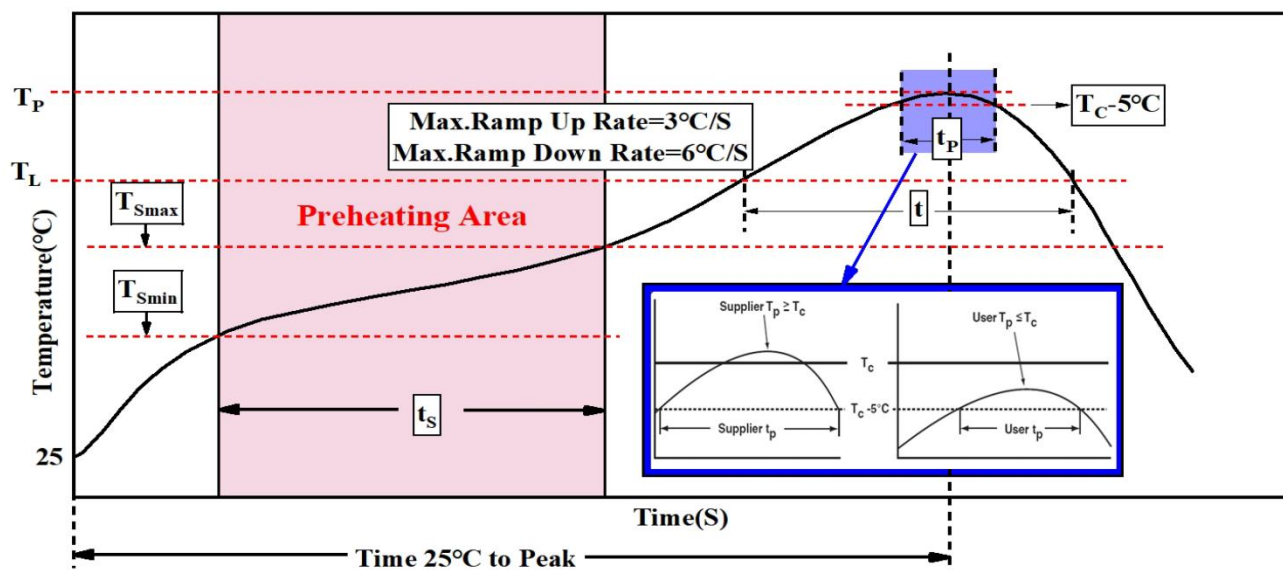
Normalized Threshold voltage



Safe Operation Area



Test Circuit
Gate Charge

Resistive Load Switching Time

Un-clamped Inductive Load Switching

Drain-Source Body Diode Reverse Recovery


Temperature Profile for IR Reflow Soldering


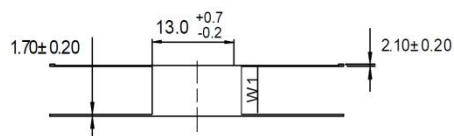
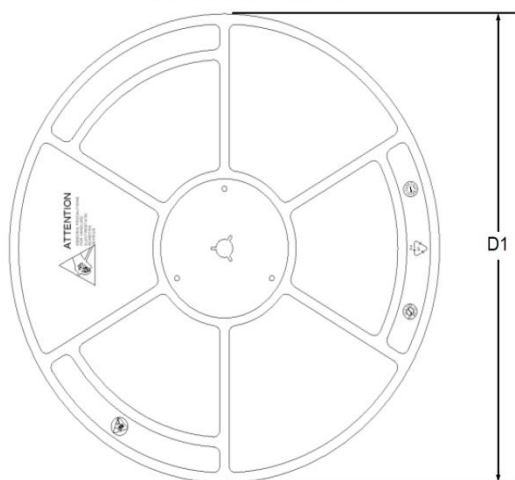
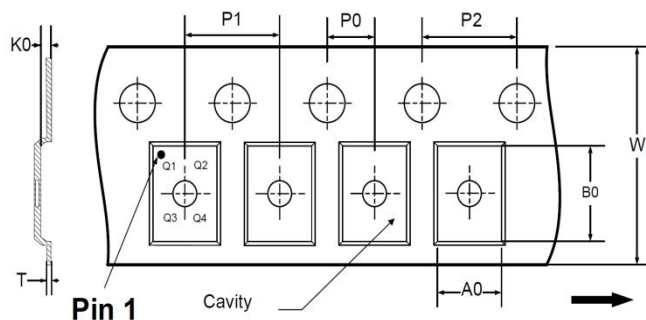
Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{Smin})	100°C	150°C
Temperature max (T_{Smax})	150°C	200°C
Time (T_{Smin} to T_{Smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{Smax} to T_P)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217°C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature e (T_P)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_P)** within 5°C of the specified classification temperature (T_C)	20** seconds	30** seconds
Average ramp-down rate (T_P to T_{Smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_P) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_P) is defined as a supplier minimum and a user maximum		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_C)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

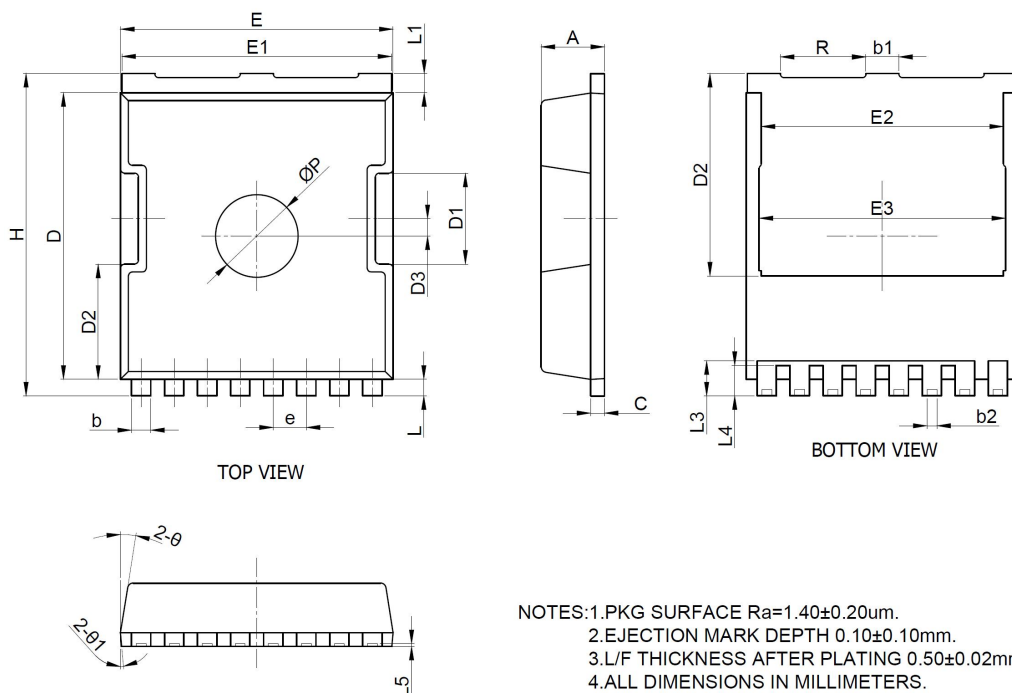
Table 2. Pb-free Process – Classification Temperatures (T_C)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

TOLL Reel Information
REEL DIMENSIONS

TAPE DIMENSIONS


- A0: Dimension designed to accommodate the component width
B0: Dimension designed to accommodate the component length
K0: Dimension designed to accommodate the component thickness
W: Overall width of the carrier tape
P0: Pitch between successive cavity centers and sprocket hole
P1: Pitch between successive cavity centers
P2: Pitch between sprocket hole
T: Tape material thickness
D1: Reel Diameter
W1: Reel Width

DIMENSIONS										(Unit: mm)
Reel	D1	W1								Material
	330	24.4								Hips
Tape	P0	P1	P2	W	A0	B0	K0	T	Pin 1 Quadrant	Material
	2	4	12	24	10.3	12.1	2.6	0.35	Q1	PC
All dimensions are nominal										

TOLL Package Information


Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	2.20	2.30	2.40
b	0.60	0.70	0.80
b1	1.10	1.20	1.30
b2	0.36 REF.		
C	0.40	0.50	0.60
D	10.30	10.40	10.50
D1	3.20	3.30	3.40
D2	4.08	4.18	4.28
D3	0.53	0.63	0.73
D4	7.35 REF.		
E	9.80	9.9	10.00
E1	9.70	9.80	9.90
E2	8.80 REF.		
E3	8.95 REF.		
e	1.20 BSC.		
H	11.5	11.7	11.90
L	0.5	0.6	0.7
L1	0.60	0.7	0.80
L2	0.10 REF.		
L3	1.27 REF.		
L4	1.10 REF.		
P	2.00	3.00	4.00
R	3.00	3.10	3.20
θ	7°	9°	11°
θ1	3°	5°	7°